



256MB – 2x16Mx64 SDRAM UNBUFFERED

FEATURES

- PC100 and PC133 compatible
- Burst Mode Operation
- Auto and Self Refresh capability
- LVTTTL compatible inputs and outputs
- Serial Presence Detect with EEPROM
- Fully synchronous: All signals are registered on the positive edge of the system clock
- Programmable Burst Lengths: 1, 2, 4, 8 or Full Page
- 3.3V $\pm$ 0.3V Power Supply
- 168 pin DIMM JEDEC

DESCRIPTION

The W3DG6434V is a 2x16Mx64 synchronous DRAM module which consists of sixteen 16Mx8 SDRAM components in TSOP II package and one 2K EEPROM in an 8 pin TSSOP package for Serial Presence Detect which are mounted on a 168 pin DIMM multilayer FR4 Substrate.

* This product is subject to change without notice.

NOTE: Consult factory for availability of:

- Lead-Free or RoHS Products
- Vendor source control options
- Industrial temperature option

PIN CONFIGURATIONS (FRONT SIDE/BACK SIDE)

PIN	FRONT	PIN	FRONT	PIN	FRONT	PIN	BACK	PIN	BACK	PIN	BACK
1	V _{SS}	29	DQM1	57	DQ18	85	V _{SS}	113	DQM5	141	DQ50
2	DQ0	30	CS0#	58	DQ19	86	DQ32	114	CS1#	142	DQ51
3	DQ1	31	DNU	59	V _{CC}	87	DQ33	115	RAS#	143	V _{CC}
4	DQ2	32	V _{SS}	60	DQ20	88	DQ34	116	V _{SS}	144	DQ52
5	DQ3	33	A0	61	NC	89	DQ35	117	A1	145	NC
6	V _{CC}	34	A2	62	*V _{REF}	90	V _{CC}	118	A3	146	*V _{REF}
7	DQ4	35	A4	63	CKE1	91	DQ36	119	A5	147	DNU
8	DQ5	36	A6	64	V _{SS}	92	DQ37	120	A7	148	V _{SS}
9	DQ6	37	A8	65	DQ21	93	DQ38	121	A9	149	DQ53
10	DQ7	38	A10/AP	66	DQ22	94	DQ39	122	BA0	150	DQ54
11	DQ8	39	BA1	67	DQ23	95	DQ40	123	A11	151	DQ55
12	V _{SS}	40	V _{CC}	68	V _{SS}	96	V _{SS}	124	V _{CC}	152	V _{SS}
13	DQ9	41	V _{CC}	69	DQ24	97	DQ41	125	CK1	153	DQ56
14	DQ10	42	CK0	70	DQ25	98	DQ42	126	*A12	154	DQ57
15	DQ11	43	V _{SS}	71	DQ26	99	DQ43	127	V _{SS}	155	DQ58
16	DQ12	44	DNU	72	DQ27	100	DQ44	128	CKE0	156	DQ59
17	DQ13	45	CS2#	73	V _{CC}	101	DQ45	129	CS3#	157	V _{CC}
18	V _{CC}	46	DQM2	74	DQ28	102	V _{CC}	130	DQM6	158	DQ60
19	DQ14	47	DQM3	75	DQ29	103	DQ46	131	DQM7	159	DQ61
20	DQ15	48	DNU	76	DQ30	104	DQ47	132	*A13	160	DQ62
21	*CB0	49	V _{CC}	77	DQ31	105	*CB4	133	V _{CC}	161	DQ63
22	*CB1	50	NC	78	V _{SS}	106	*CB5	134	NC	162	V _{SS}
23	V _{SS}	51	NC	79	CK2	107	V _{SS}	135	NC	163	CK3
24	NC	52	*CB2	80	NC	108	NC	136	*CB6	164	NC
25	NC	53	*CB3	81	WP***	109	NC	137	*CB7	165	**SA0
26	V _{CC}	54	V _{SS}	82	**SDA	110	V _{CC}	138	V _{SS}	166	**SA1
27	WE#	55	DQ16	83	**SCL	111	CAS#	139	DQ48	167	**SA2
28	DQM0	56	DQ17	84	V _{CC}	112	DQM4	140	DQ49	168	V _{CC}

PIN NAMES

A0 – A11	Address input (Multiplexed)
BA0-1	Select Bank
DQ0-63	Data Input/Output
CK0-CK3	Clock input
CKE0,CKE1	Clock Enable input
CS0#-CS3#	Chip select Input
RAS#	Row Address Strobe
CAS#	Column Address Strobe
WE#	Write Enable
DQM0-7#	DQM
V _{CC}	Power Supply (3.3V)
V _{SS}	Ground
SDA	Serial data I/O
SCL	Serial clock
DNU	Do not use
NC	No Connect
WP	Write Protect

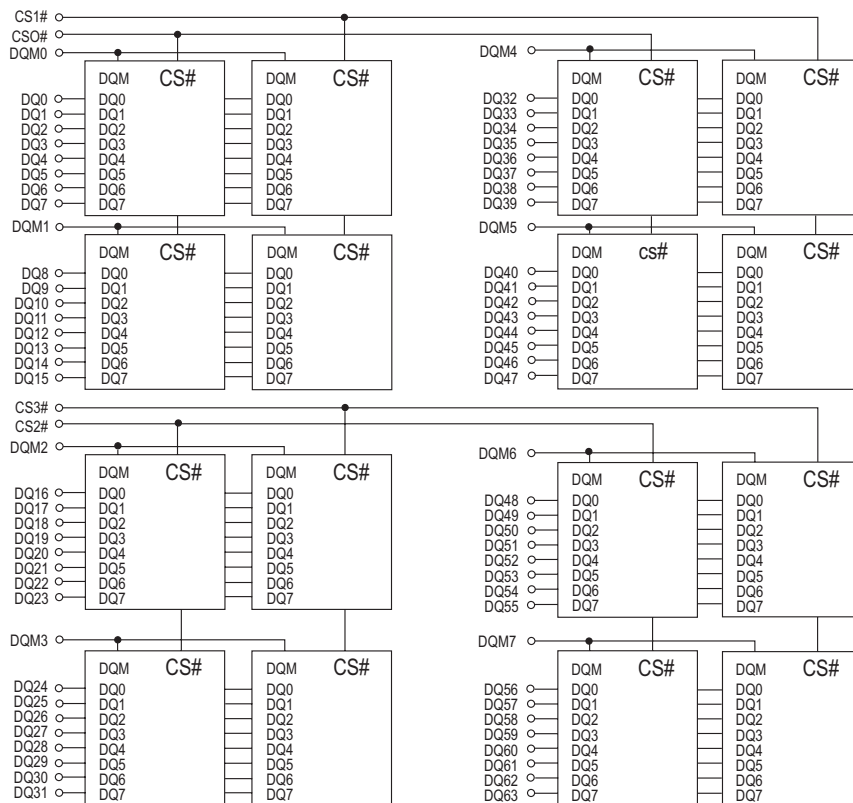
* These pins are not used in this module.

** These pins should be NC in the system which does not support SPD.

*** WP available on the W3DG6334V-D2.



FUNCTIONAL BLOCK DIAGRAM

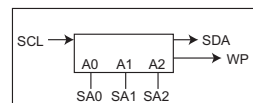


A0 ~ A12, BA0 & 1 → SDRAM
RAS# → SDRAM
CAS# → SDRAM
WE# → SDRAM
CKE0 → SDRAM

Vcc
10KΩ
CKE1 → SDRAM

10Ω
DQn → Every DQpin of SDRAM

Vcc
Two 0.1μF Capacitors
per each SDRAM
Vss
To all SDRAMs





ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Units
Voltage on any pin relative to V _{SS}	V _{IN} , V _{OUT}	-1.0 ~ 4.6	V
Voltage on V _{CC} supply relative to V _{SS}	V _{CC} , V _{CCA}	-1.0 ~ 4.6	V
Storage Temperature	TSTG	-55 ~ +150	°C
Power Dissipation	PD	16	W
Short Circuit Current	IOS	50	mA

Note: Permanent device damage may occur if "ABSOLUTE MAXIMUM RATINGS" are exceeded.
Functional operation should be restricted to recommended operating condition.
Exposure to higher than recommended voltage for extended periods of time could affect device reliability.

RECOMMENDED DC OPERATING CONDITIONS

Voltage Referenced to: V_{SS} = 0V, 0°C ≤ T_A ≤ +70°C

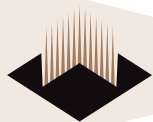
Parameter	Symbol	Min	Typ	Max	Unit	Note
Supply Voltage	V _{CC}	3.0	3.3	3.6	V	
Input High Voltage	V _{IH}	2.0	3.0	V _{CCA} +0.3	V	1
Input Low Voltage	V _{IL}	-0.3	—	0.8	V	2
Output High Voltage	V _{OH}	2.4	—	—	V	I _{OH} = -2mA
Output Low Voltage	V _{OL}	—	—	0.4	V	I _{OL} = -2mA
Input Leakage Current	I _{LI}	-10	—	10	μA	3

Note:
1. V_{IH} (max)= 5.6V AC. The overshoot voltage duration is ≤ 3ns.
2. V_{IL} (min)= -2.0V AC. The undershoot voltage duration is ≤ 3ns.
3. Any input 0V ≤ V_{IN} ≤ V_{CC}
Input leakage currents include Hi-Z output leakage for all bi-directional buffers with Tri-State outputs.

CAPACITANCE

T_A = 25°C, f = 1MHz, V_{CC} = 3.3V, V_{REF}=1.4V ± 200mV

Parameter	Symbol	Max	Unit
Input Capacitance (A0-A12)	C _{IN1}	65	pF
Input Capacitance (RAS#,CAS#,WE#)	C _{IN2}	65	pF
Input Capacitance (CKE0-CKE1)	C _{IN3}	35	pF
Input Capacitance (CLK0-CLK3)	C _{IN4}	16	pF
Input Capacitance (CS0#-CS3#)	C _{IN5}	20	pF
Input Capacitance (DQM0-DQM7)	C _{IN6}	11	pF
Input Capacitance (BA0-BA1)	C _{IN7}	65	pF
Data input/output capacitance (DQ0-DQ63)	C _{OUT}	15	pF



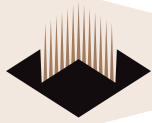
OPERATING CURRENT CHARACTERISTICS

 $V_{CC} = 3.3V$, $0^{\circ}C \leq T_A \leq 70^{\circ}C$

Parameters	Symbol	Conditions	Versions		Units	Note
			133	100		
Operating Current (One bank active)	I_{CC1}	Burst Length = 1 $t_{RC} \geq t_{RC(min)}$ $I_{OL} = 0mA$	1440	1440	mA	1
Precharge Standby Current in Power Down Mode	I_{CC2P}	$CKE \leq V_{IL(max)}$, $t_{CC} = 10ns$	32		mA	
	I_{CC2PS}	$CKE \& CK \leq V_{IL(max)}$, $t_{CC} = \infty$	32		mA	
Precharge Standby Current in Non-Power Down Mode	I_{CC2N}	$CKE \geq V_{IH(min)}$, $CS \geq V_{IH(min)}$, $t_{CC} = 10ns$ Input signals are charged one time during 20	320		mA	
	I_{CC2NS}	$CKE \geq V_{IH(min)}$, $CK \leq V_{IL(max)}$, $t_{CC} = \infty$ Input signals are stable	160		mA	
Active standby current in power- down mode	I_{CC3P}	$CKE \geq V_{IL(max)}$, $t_{CC} = 10ns$	80		mA	
	I_{CC3PS}	$CKE \& CK \leq V_{IL(max)}$, $t_{CC} = \infty$	80			
Active standby in current non power-down mode	I_{CC3N}	$CKE \geq V_{IH(min)}$, $CS \geq V_{IH(min)}$, $t_{CC} = 10ns$ Input signals are charged one time during 20ns	480		mA	
	I_{CC3NS}	$CKE \geq V_{IH(min)}$, $CK \leq V_{IL(max)}$, $t_{CC} = \infty$ input signals are stable	400		mA	
Operating current (Burst mode)	I_{CC4}	$I_O = mA$ Page burst 4 Banks activated $t_{CCD} = 2CK$	1760	1760	mA	1
Refresh current	I_{CC5}	$t_{RC} \geq t_{RC(min)}$	3200	3200	mA	2
Self refresh current	I_{CC6}	$CKE \leq 0.2V$	32		mA	

Notes:

1. Measured with outputs open.
2. Refresh period is 64ms.



ORDERING INFORMATION

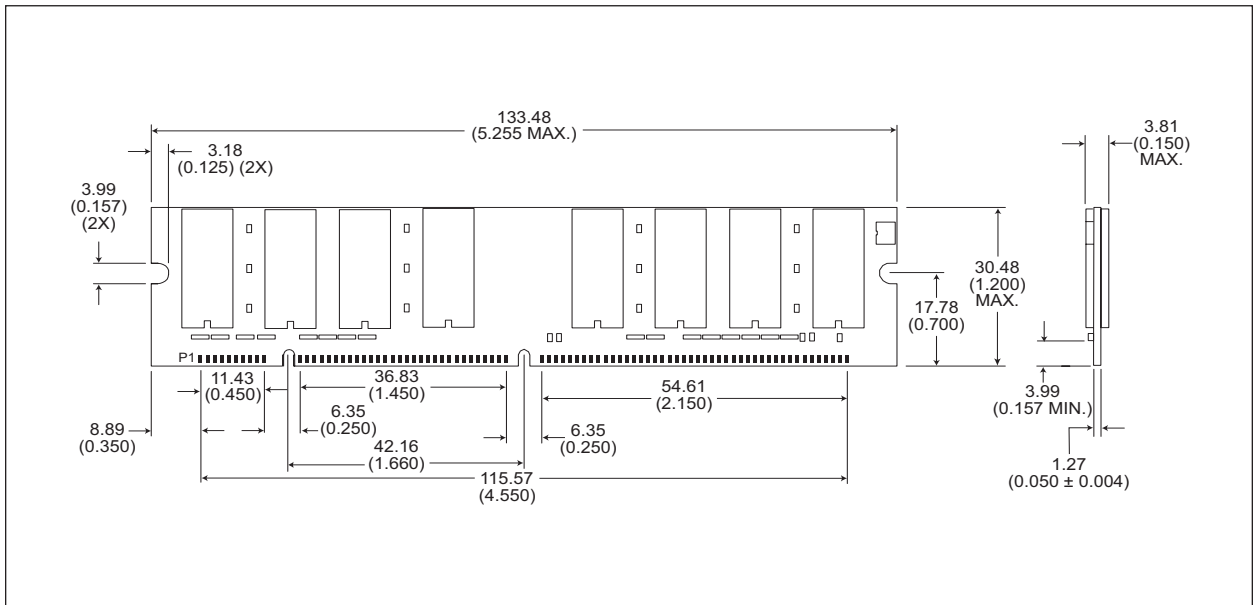
Part Number	Speed	CAS Latency	Height*
W3DG6434V10D2	100MHz	CL=2	30.48 (1.20")
W3DG6434V7D2	133MHz	CL=2	30.48 (1.20")
W3DG6434V75D2	133MHz	CL=3	30.48 (1.20")

Part Number	Speed	CAS Latency	Height*
W3DG6334V10D2	100MHz	CL=2	30.48 (1.20")
W3DG6334V7D2	133MHz	CL=2	30.48 (1.20")
W3DG6334V75D2	133MHz	CL=3	30.48 (1.20")

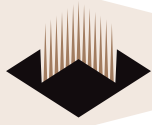
Note: Available with "WP" Write Protect on pin 81.

- NOTES:
- Consult Factory for availability of Lead-Free or RoHS products. (F = Lead-Free, G = RoHS Compliant)
 - Vendor specific part numbers are used to provide memory components source control. The place holder for this is shown as lower case "x" in the part numbers above and is to be replaced with the respective vendors code. Consult factory for qualified sourcing options. (M = Micron, S = Samsung & consult factory for others)
 - Consult factory for availability of industrial temperature (-40°C to 85°C) option

PACKAGE DIMENSIONS



ALL DIMENSIONS ARE IN MILLIMETERS AND (INCHES)



Document Title

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Revision History

Rev #	History	Release Date	Status
Rev A	Created	12-18-01	Advanced
Rev B	Added "part number" to order table on page 6	2-13-01	Advanced
Rev C	Added "WP" write protect to pin 81	4-10-02	Advanced
Rev D	Corrected mechanical drawing	5-21-02	Advanced
Rev 0	Changed from Advanced to Final	8-19-02	Final
Rev 1	1.1 Updated CAP & I _{DD} specs	7-2004	Final
	1.2 Removed "ED" from part number		
	1.3 Added new title page		